In the Claims

Claims 1-72 (cancelled).

Claim 73 (currently amended): A semiconductor processing patterning method, comprising:

forming a first and second resist layers over a surface of a silicon-comprising substrate, the first layer being both beneath the second layer and having a thickness which is less than a thickness of the second resist layer;

forming a mask pattern over the silicon-comprising substrate, the mask pattern comprising a plurality of pillars comprising the material of the first and second resist layers, wherein individual pillars of the pattern are comprised by:

the material of the first resist layer ~~of the mask pattern comprises~~ defining opposing sidewalls in at least one cross section, the material of the first resist layer extending continuously between the opposing sidewalls of the individual pillar of the mask pattern;

the material of the second resist layer ~~of the mask pattern comprises~~ defining opposing sidewalls in the one cross section, the material of the second resist layer extending continuously between the opposing sidewalls of the individual pillar of the mask pattern; and

an entirety of the opposing sidewalls of the material of the first resist layer received laterally inward of an entirety of the opposing sidewalls of the material of the second resist layer in the one cross section; and

etching material of the silicon-comprising substrate using the mask pattern as a mask.

Claim 74 (currently amended): The method of claim 73 wherein the first and second resist layers comprise different compositions ~~as initially formed~~.

Claim 75 (previously presented): The method of claim 73 wherein the first resist layer is photosensitive to electromagnetic radiation at a wavelength of no greater than about 325 nm.

Claim 76 (previously presented): The method of claim 73 wherein both the first and second resist layers comprise negative resist.

Claim 77 (previously presented): The method of claim 73 wherein both the first and second resist layers comprise positive resist.

Claim 78 (currently amended): The method of claim 73 wherein the first resist layer comprises ~~at least one of~~ 1-methoxy-2-propanol and ethyl lactate and the second resist layer comprises ~~at least one of~~ cyclohexanone and 2-heptanone.

Claim 79 (previously presented): The method of claim 73 wherein the first resist layer has a thickness which is less than a total thickness of all layers received over the first resist layer.

Claim 80 (previously presented): The method of claim 73 wherein the first resist layer has a thickness which is less than or equal to about 50% of a total thickness of the first resist layer and all layers received over the first resist layer.

Claim 81 (previously presented): The method of claim 73 wherein the first resist layer has a thickness which is less than or equal to about 25% of a total thickness of the first resist layer and all layers received over the first resist layer.

Claim 82 (previously presented): The method of claim 73 wherein the first resist layer has a thickness which is less than or equal to about 10% of a total thickness of the first resist layer and all layers received over the first resist layer.

Claim 83 (previously presented): The method of claim 73 wherein the first resist layer has a thickness which is less than or equal to about 5% of a total thickness of the first resist layer and all layers received over the first resist layer.

Claim 84 (previously presented): The method of claim 73 wherein the opposing sidewalls of the first resist layer are at least partially curved in the one cross section.

Claim 85 (previously presented): The method of claim 73 wherein the opposing sidewalls of the first resist layer and the opposing sidewalls of the second resist layer are of different shapes in the one cross section.

Claim 86 (currently amended): A semiconductor processing patterning method, comprising:

forming a first positive resist layer over a surface of a silicon-comprising substrate;

forming a second positive resist layer over the first positive resist layer, the first positive resist layer having a thickness less than the second positive resist layer;

forming a mask pattern over the silicon-comprising substrate, the mask pattern comprising a plurality of pillars comprising the material of the first and second positive resist layers, wherein individual pillars of the pattern are comprised by:

the material of the first positive resist layer ~~comprises~~ defining opposing sidewalls in at least one cross section, the material of the first positive resist layer extending continuously between the opposing sidewalls of the material of the first positive resist layer of the ~~mask pattern~~ individual pillar;

the material of the second positive resist layer ~~comprises~~ defining opposing sidewalls in at least the one cross section, the material of the second positive resist layer extending continuously between the opposing sidewalls of the material of the second positive resist layer of the ~~mask pattern~~ individual pillar; and

at least a portion of the opposing sidewalls of the material of the first positive resist layer of the mask pattern are recessed laterally

inward of at least a portion of opposing sidewalls of the material of the second positive resist layer in the one cross section; and

etching material of the silicon-comprising substrate using the mask pattern as a mask.

Claim 87 (previously presented): The method of claim 86 wherein the first positive resist layer is photosensitive to electromagnetic radiation at a wavelength of no greater than about 325 nm.

Claim 88 (previously presented): The method of claim 86 wherein the second positive resist layer is formed on the first positive resist layer.

Claim 89 (previously presented): The method of claim 86 wherein the first positive resist layer comprises 1-methoxy-2-propanol and the second positive resist layer comprises cyclohexanone and 2-heptanone.

Claim 90 (previously presented): The method of claim 86 wherein the first positive resist layer has a thickness which is less than a total thickness of all layers received over the first positive resist layer.

Claims 91-92 (cancelled)

Claim 93 (previously presented): The method of claim 86 wherein the first positive resist layer has a thickness which is less than about 5% of a total thickness of the first positive resist layer and all layers received over the first positive resist layer.

Claim 94 (previously presented): The method of claim 86 wherein the opposing sidewalls of the first positive resist layer are at least partially curved in the one cross section.

Claim 95 (previously presented): The method of claim 86 wherein an entirety of the opposing sidewalls of the first positive resist layer are recessed laterally inward of the opposing sidewalls of the second positive resist layer in the one cross section.